



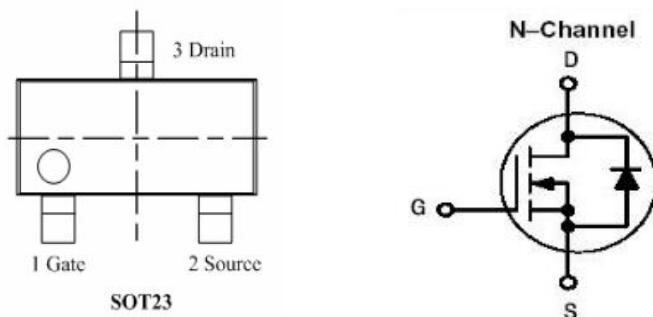
深圳瑞之辰科技有限公司

RZC3400
30V N-Channel MOSFET

GENERAL DESCRIPTION

The RZC3400 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. This device is suitable for used as a load switch or in Pulse width modulation applications.

PIN CONFIGURATION



FEATURES

- $V_{DS(max)} = 30V$;
- $I_{D(max)} = 3.0A$ (SOT23)
 $I_{D(max)} = 5.7A$ (SOT23-3)
- Low on-state resistance
 $R_{DS(on)} = 35m\Omega$ TYP. ($V_{GS} = 10V$)
 $R_{DS(on)} = 40m\Omega$ TYP. ($V_{GS} = 4.5V$)
 $R_{DS(on)} = 60m\Omega$ TYP. ($V_{GS} = 2.5V$)

APPLICATIONS

- Power Management in Notebook Computer
- Portable Equipment
- Battery Powered Systems.

ORDERING INFORMATION

Part Number	Package	Top Marking	Packing
RZC3400	SOT-23	A09T	3000PCS/Real
RZC3400C	SOT23-3	A09T	3000PCS/Real



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RZC3400
30V N-Channel MOSFET**MAXIMUM RATINGS** ($T_a = 25^\circ\text{C}$)

Parameter	Symbol		Value	Units	
Drain to Source Voltage	V_{DSS}		30	V	
Gate to Source Voltage	V_{GSS}		± 12	V	
Continuous Drain Current(SOT23)	25°C	I_D	3	A	
	85°C		2.4	A	
Continuous Drain Current(SOT23-3)	25°C	I_D	5.7	A	
	85°C		4.5	A	
Pulsed Drain Current(SOT23)	$I_{D(\text{pulse})1}$		12	A	
Pulsed Drain Current(SOT23-3)	$I_{D(\text{pulse})2}$		22.8	A	
Maximum Power Dissipation	SOT23	P_D	0.8	W	
	SOT23-3		1.0		
Operating Junction Temperature	T_J		+150	°C	
Storage Temperature	T_{STG}		-55-+150	°C	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L		260	°C	



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30V N-Channel MOSFET**ELECTRICAL CHARACTERISTICS (TA = 25°C)**

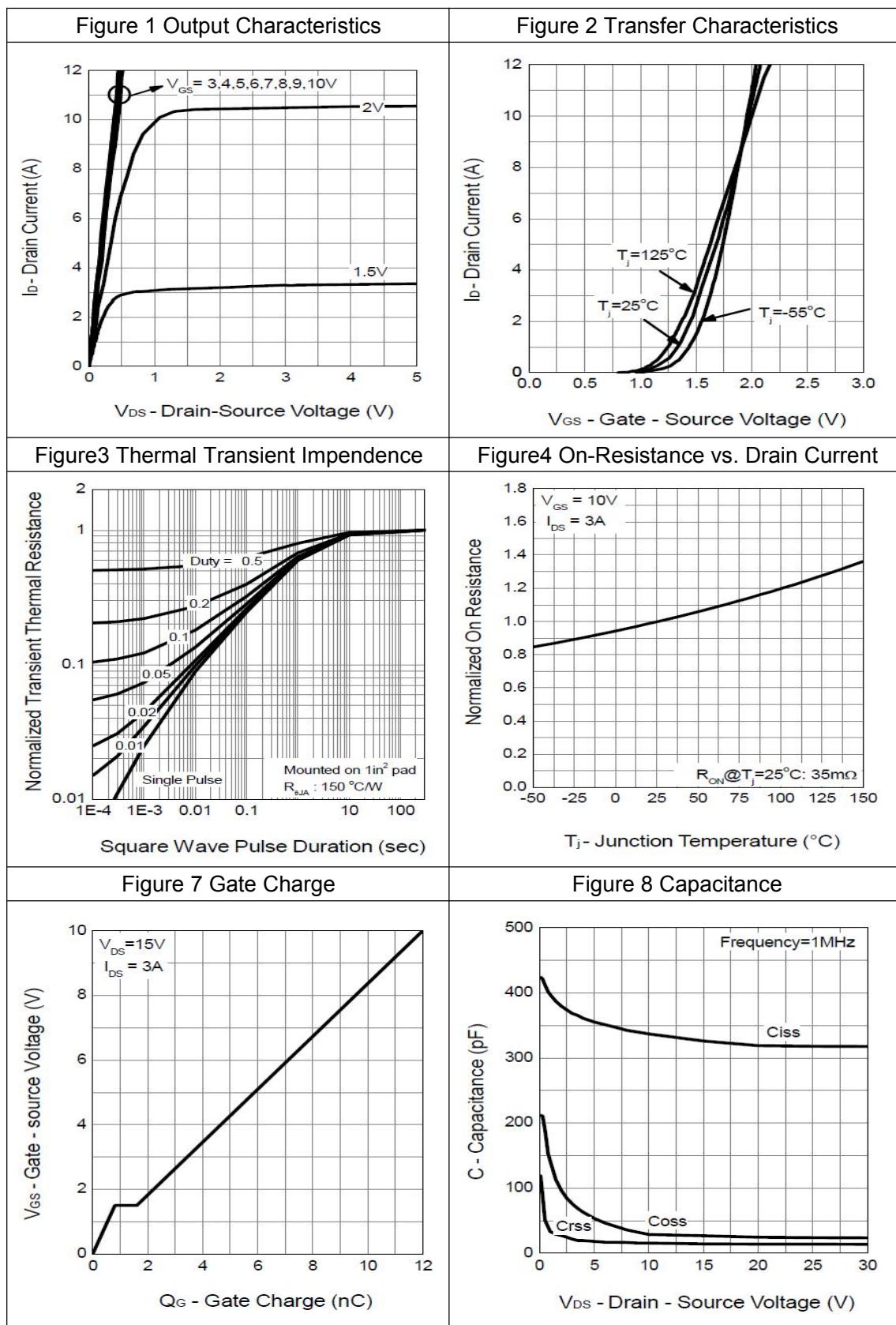
Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX	Units
Drain-Source Breakdown Voltage	BVDSS	V _{GS} =0V, I _{DS} =250μA	30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30V, V _{GS} =0V			1	μA
Gate Leakage Current	I _{GSS}	V _{GS} =±12V, V _{DS} =0V			±100	nA
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D = 250μA	0.5	0.7	1.0	V
Drain to Source On-state Resistance	R _{DS(on)}	V _{GS} = 10V, I _D =3.0A		35	50	mΩ
		V _{GS} = 4.5V, I _D =3.0A		40	55	mΩ
		V _{GS} = 2.5V, I _D =2.0A		60	80	mΩ
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =15V, f=1.0MHZ		320		pF
Output Capacitance	C _{oss}			25		pF
Reverse Transfer Capacitance	C _{rss}			15		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} =10V, I _D =1.0A, V _{GS} =4.5V, R _G =0.2Ω		11	22	nS
Rise Time	t _r			17	32	nS
Turn-off Delay Time	t _{d(off)}			37	68	nS
Fall Time	t _f			20	38	nS
Total Gate Charge	Q _G	V _{DD} =10V, I _D =1.0A, V _{GS} =4.5V,		12	16	nC
Gate to Source Charge	Q _{GS}			0.8		nC
Gate to Drain Charge	Q _{GD}			0.8		nC
Drain-Source Diode Forward Voltage	V _{SD}	I _S =2.8A, V _{GS} =0V		0.7	1.3	V



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TYPICAL CHARACTERISTICS (25°C unless noted)





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Figure 9 Source-Drain Diode Forward Voltage

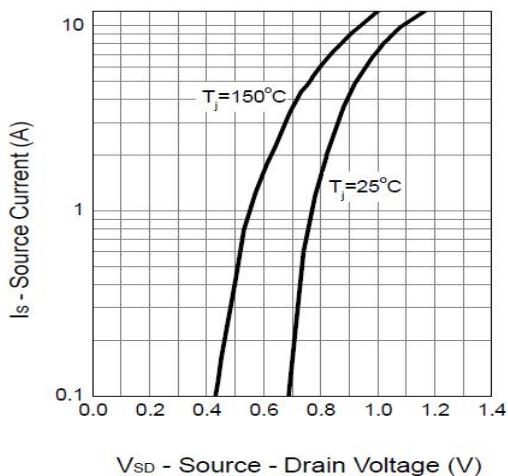
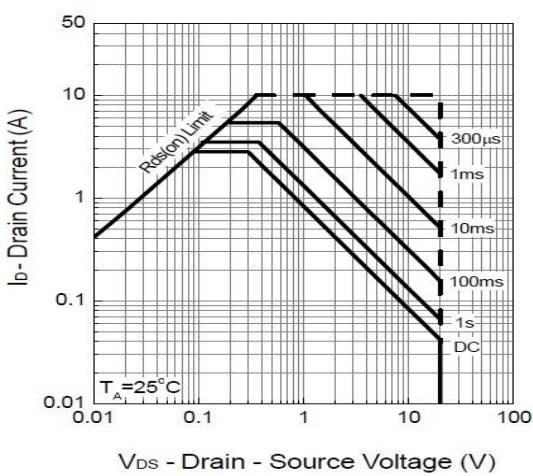


Figure 10 Safe Operation Area



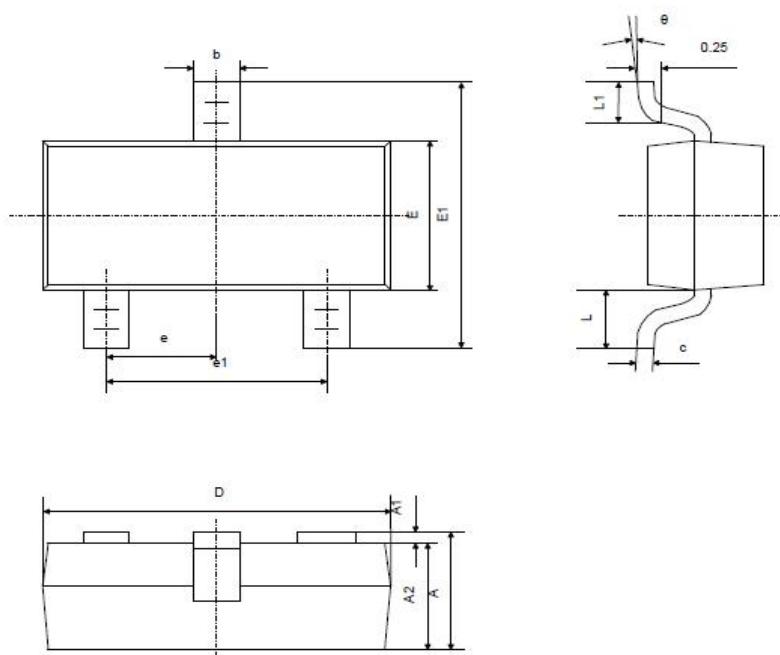


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PACKAGE DIMENSIONS

SOT-23



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.889	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	6°

Note:

- Dimension D does not include mold flash, protrusions or gate burrs. mold flash, protrusions or gate burrs shall not exceed 0.10mm per side.
- Dimension E1 does not include inter-lead flash or protrusion. Inter-lead flash or protrusion shall not exceed 0.1mm per side.

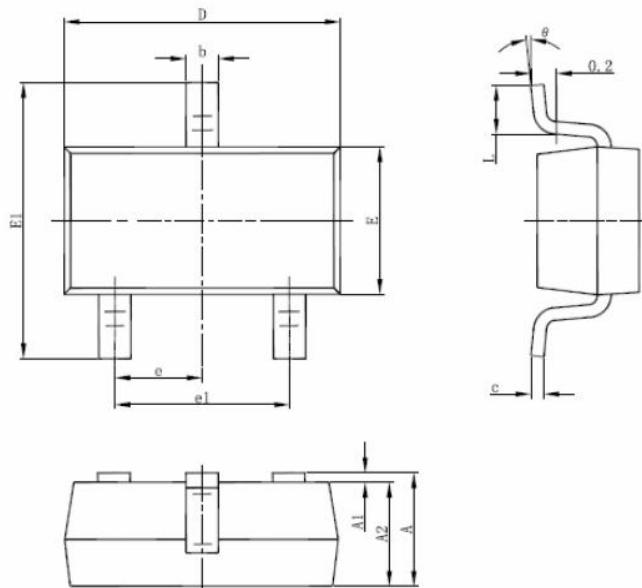


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PACKAGE DIMENSIONS

SOT23-3



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

Note:

- Dimension D does not include mold flash, protrusions or gate burrs. mold flash, protrusions or gate burrs shall not exceed 0.10mm per side.
- Dimension E1 does not include inter-lead flash or protrusion. Inter-lead flash or protrusion shall not exceed 0.1mm per side.